

3A Sink and Source DDR Termination Regulator

Features

- VIN Voltage: Supports 2.5V or 3.3V Power Rail
- VLDOIN Voltage Range: 1.1V to 3.5V
- Sink and Source Termination Regulator Includes Droop Compensation
- PGOOD to Monitor Output Regulation
- Remote Sensing (VOSNS)
- REFIN Input Allows for Flexible Input Tracking Either Directly or Through Resistor Divider
- $\pm 25\text{mA}$ Buffered Reference (REFOUT)
- Built-in Soft Start, UVLO, and OCL
- Supports DDR, DDR2, DDR3, DDR3L, Low-Power DDR3, and DDR4 VTT Applications
- Thermal Shutdown

Application

- Memory Termination Regulator for DDR, DDR2, DDR3, DDR3L, Low-Power DDR3 and DDR4
- Notebooks, Desktops, and Servers
- Telecom ,Datacom and Base Stations
- LCD-TVs and PDP-TVs
- Copiers and Printers, Set-Top Boxes

Description

The TMI62033 is a 3A sink and source double data rate (DDR) termination regulator. It supports a remote sensing function and all power requirements for DDR, DDR2, DDR3, DDR3L, Low-Power DDR3 and DDR4 VTT bus termination.

The TMI62033 maintains a fast transient response and requires a minimum output capacitance of only $20\mu\text{F}$ for low-cost, low-noise systems where space is a key consideration. In addition, the TMI62033 provides an open-drain PGOOD signal to monitor the output regulation for VTT regulation indication and an EN signal that can be used to discharge VTT for DDR applications.

The TMI62033 is available in the thermally efficient 10-pin 3x3 DFN thermal pad package, and is rated both Green and Pb-free.

Typical Application

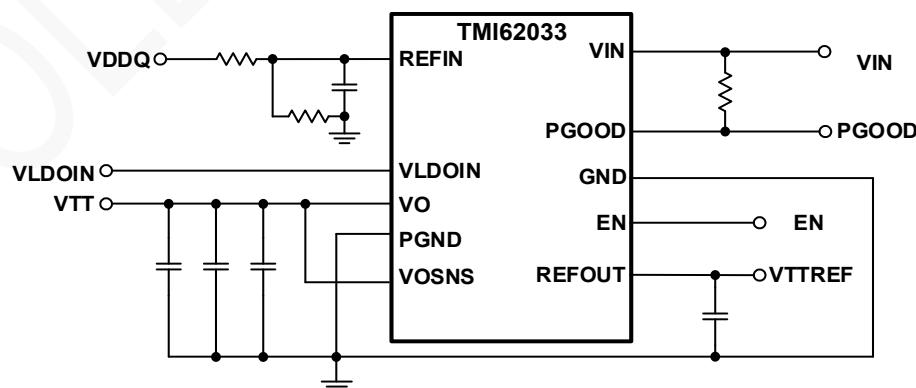
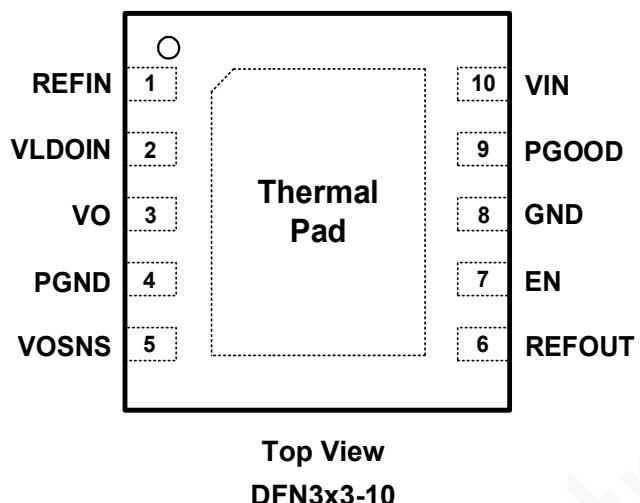


Figure 1. TMI62033 Typical Application Circuit

Package



Top Marking: T62033/XXXXX (T62033: Device Code, XXXXX: Inside Code)

Order Information

Part Number	Package	Top Marking	Quantity/Reel
TMI62033	DFN3x3-10	T62033 XXXXX	5000

TMI62033 devices are Pb-free and RoHS compliant.

Pin Functions

Pin	Name	Function
1	REFIN	Reference input pin.
2	VLDOIN	LDO power supply input pin.
3	VO	LDO power output pin.
4	PGND	Power ground for the LDO.
5	VOSNS	Voltage sense input for the LDO. Connect to positive terminal of the output capacitor or the load.
6	REFOUT	Reference output. Connect to GND through 0.1µF ceramic capacitor.
7	EN	For DDR VTT application. For any other application, use the EN pin as the ON/OFF function.
8	GND	Ground pin.
9	PGOOD	Open-drain, power-good output pin.
10	VIN	2.5V/3.3V Power supply input pin. A 1µF or larger ceramic capacitor from IN to ground (as close as possible to VIN pin) is required to reduce the jitter from previous-stage power supply.
Thermal Pad		Thermal Pad must be connected to a large-area ground plane to maximum the thermal performance.

Absolute Maximum Ratings (Note 1)

Parameter	Min	Max	Unit
REFIN, VIN, VLDOIN, VOSNS Voltage	-0.3	3.6	V
EN Voltage	-0.3	6.5	V
PGND to GND	-0.3	0.3	V
REFOUT, VO Voltage	-0.3	3.6	V
PGOOD Voltage	-0.3	6.5	V
Storage Temperature Range	-55	150	°C
Junction Temperature (Note2)	-40	150	°C

ESD Rating (Note2)

Items	Description	Value	Unit
V_{ESD_HBM}	Human Body Model for all pins	± 4000	V
V_{ESD_CDM}	Charged Device Model for all pins	± 1000	V

JEDEC specification JS-001

Recommended Operating Conditions

Items	Description	Min	Max	Unit
VIN	Supply Voltage	2.375	3.5	V
EN, VLDOIN, VOSNS	EN, LDO input and LDO Sense Voltage	-0.1	3.5	
REFIN	Reference Input Voltage	0.5	1.8	
PGOOD, VO	Power Good and LDO Output Voltage	-0.1	3.5	
REFOUT	Reference Output Voltage	-0.1	1.8	
PGND	Power Ground Voltage to GND	-0.1	0.1	
T_J (Note3)	Junction Temperature	-40	125	°C

Thermal Resistance (Note4)

Items	Description	Value	Unit
θ_{JA}	Junction-to-ambient thermal resistance	65	°C/W
$\theta_{JC(\text{top})}$	Junction-to-case(top) thermal resistance	26	°C/W
ψ_{JT}	Junction-to-case(top) characterization parameter	5.5	°C/W

Electrical Characteristics

$V_{VIN}=3.3V$, $V_{VLDOIN}=1.8V$, $V_{REFIN}=0.9V$, $V_{VOSNS}=0.9V$, $V_{EN}=V_{VIN}$, $C_{OUT}=3x10\mu F$, $T_A=25^\circ C$, and unless otherwise noted.

Symbol	Parameter	Conditions	Min	Type	Max	Units
SUPPLY CURRENT						
I_{IN}	VIN Input Current Range	$T_A = 25^\circ C$, $V_{EN}= 3.3V$, No Load		0.7	1	mA
$I_{IN(SDN)}$	VIN shutdown current	$T_A = 25^\circ C$, $V_{EN}= 0V$, $V_{REFIN}=0V$ No Load		30	80	μA
		$T_A = 25^\circ C$, $V_{EN}= 0V$, $V_{REFIN}=0.9V$ No Load		200	400	
		$T_A = 25^\circ C$, $V_{EN}= 3.3V$, No Load		1	50	
I_{LDOIN}	VLDOIN Input Current Range	$T_A = 25^\circ C$, $V_{EN}= 0V$, No Load		2	50	
I_{REFIN}	REFIN Input Current Range	$V_{EN}= 3.3V$			1	
VO OUTPUT						
VOSNS	Output DC voltage, VO	$V_{REFOUT}=1.25V$ (DDR1), $I_o= 0A$		1.25		V
			-15		15	mV
		$V_{REFOUT}=0.9V$ (DDR2), $I_o= 0A$		0.9		V
			-15		15	mV
		$V_{REFOUT}=0.75V$ (DDR3), $I_o= 0A$		0.75		V
			-15		15	mV
		$V_{REFOUT}=0.675V$ (DDR3L), $I_o= 0A$		0.675		V
			-15		15	mV
		$V_{REFOUT}=0.6V$ (DDR4), $I_o= 0A$		0.6		V
			-15		15	mV
V_{VOTOL}	Output voltage tolerance to REFOUT	$-2A < I_{VO} < 2A$	-25		25	mV
I_{VOSRCL}	VO source current Limit	With reference to REFOUT, $V_{OSNS}=90\% \times V_{REFOUT}$	3		5.5	A
I_{VOSNCL}	VO sink current Limit	With reference to REFOUT, $V_{OSNS}=110\% \times V_{REFOUT}$	3.5		5.5	A
I_{DSCHRG}	Discharge current, VO	$V_{REFIN}=0V$, $V_{VO}= 0.3V$, $V_{EN}= 0V$ $T_A = 25^\circ C$		20	30	Ω
POWERGOOD COMPAPATOR						
$V_{TH(PG)}$	VO PGOOD threshold	PGOOD window lower threshold with respect to REFOUT	-23.5	-20	-17.5	% %
		PGOOD window upper threshold with respect to REFOUT	17.5	20	23.5	
		PGOOD hysteresis		5		
$t_{PGSTUPDLY}$	PGOOD start-up delay	Start-up rising edge, VOSNS within 15% of REFOUT		2		ms
$V_{PGOODLOW}$	Output low voltage	$I_{SINK}= 4 mA$			0.4	V
$t_{PBADDLY}$	PGOOD bad delay	VOSNS is outside of the $\pm 20\%$ PGOOD window		20		μs
$I_{PGOODLK}$	Leakage current	$V_{OSNS} = V_{REFIN}$ (PGOOD high impedance), $V_{PGOOD} = V_{VIN} + 0.2V$			1	μA

Electrical Characteristics (Continued)

$V_{VIN} = 3.3V$, $V_{VLDOIN} = 1.8V$, $V_{REFIN} = 0.9V$, $V_{VOSNS} = 0.9V$, $V_{EN} = V_{VIN}$, $C_{OUT} = 3*10\mu F$, $T_A = 25^\circ C$, and unless otherwise noted.

Symbol	Parameter	Conditions	Min	Type	Max	Units
REFIN AND REFOUT						
V_{REFIN}	REFIN voltage range		0.5		1.8	V
$V_{REFINUVLO}$	REFIN under voltage lockout	REFIN rising	340	390	440	mV
$V_{REFINUVHYS}$	REFIN under voltage lockout hysteresis			60		mV
V_{REFOUT}	REFOUT voltage			REFIN		V
$V_{REFOUTTOL}$	REFOUT voltage tolerance to V_{REFIN}	-1mA < I_{REFOUT} < 1mA $V_{REFIN} = 1.25 V$	-12		12	mV
		-1mA < I_{REFOUT} < 1mA $V_{REFIN} = 0.9 V$	-12		12	
		-1mA < I_{REFOUT} < 1mA $V_{REFIN} = 0.75 V$	-12		12	
		-1mA < I_{REFOUT} < 1mA $V_{REFIN} = 0.675V$	-12		12	
		-1mA < I_{REFOUT} < 1mA $V_{REFIN} = 0.6 V$	-12		12	
$I_{REFOUTSRCL}$	REFOUT source current limit	$V_{REFOUT} = 0 V$	25	50		mA
$I_{REFOUTSNCL}$	REFOUT sink current limit	$V_{REFOUT} = 0 V$	25	50		mA
VIN UVLO AND EN LOGIC THRESHOLD						
U_{VINUV}	UVLO threshold of VIN	VIN rising, $T_A = 25^\circ C$		2.3	2.375	V
		Hysteresis		150		mV
V_{ENIH}	High-level threshold voltage	VIN=3.3V		1.35	1.7	V
V_{ENIL}	Low-level threshold voltage	VIN=3.3V	0.5	1.05		
V_{ENYST}	Hysteresis voltage	VIN=3.3V		0.3		
I_{ENLEAK}	Logic input leakage current	EN, $T_A = 25^\circ C$	-1		1	µA
THERMAL SHUTDOWN						
T_{SON}	Thermal shutdown threshold	Shutdown temperature		155		°C
		Hysteresis		25		

Note 1: Absolute Maximum Ratings are those values beyond which the life of a device may be impaired.

Note 2: Devices are ESD sensitive. Handling precaution is recommended.

Note 3: T_J is calculated from the ambient temperature T_A and power dissipation P_D according to the following formula: $T_J = T_A + P_D \times \theta_{JA}$.

Note 4: Measured on JESD51-7, 4-layer PCB.

Block Diagram

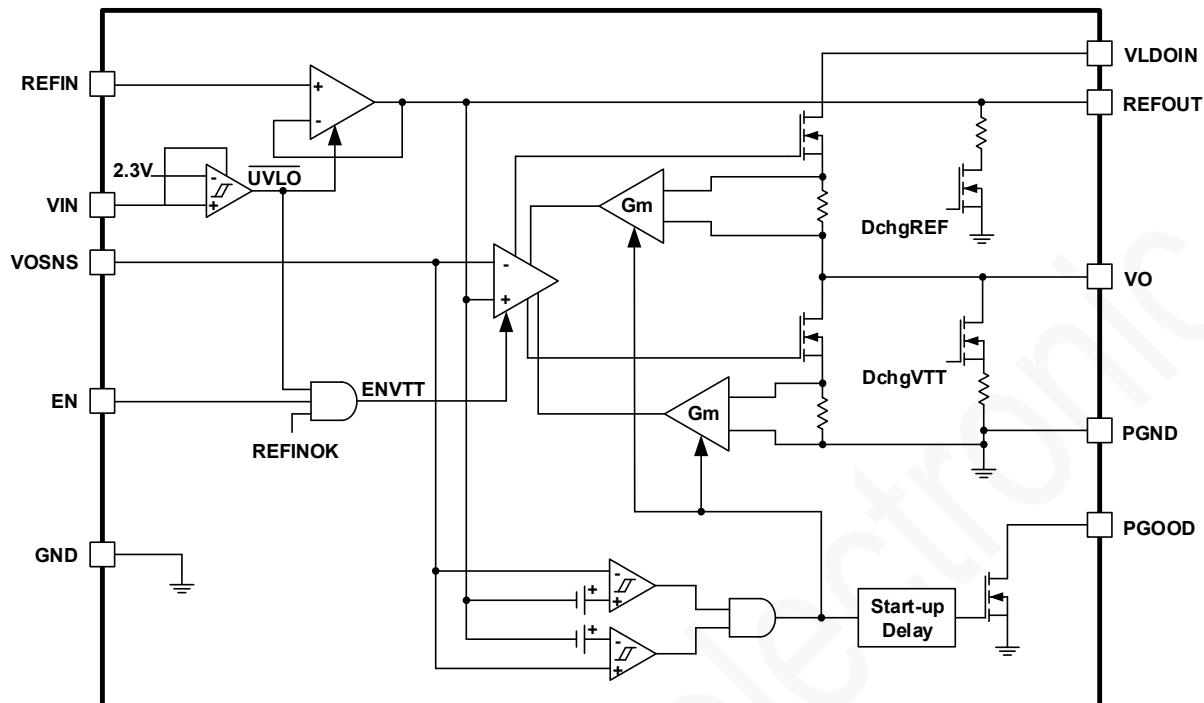
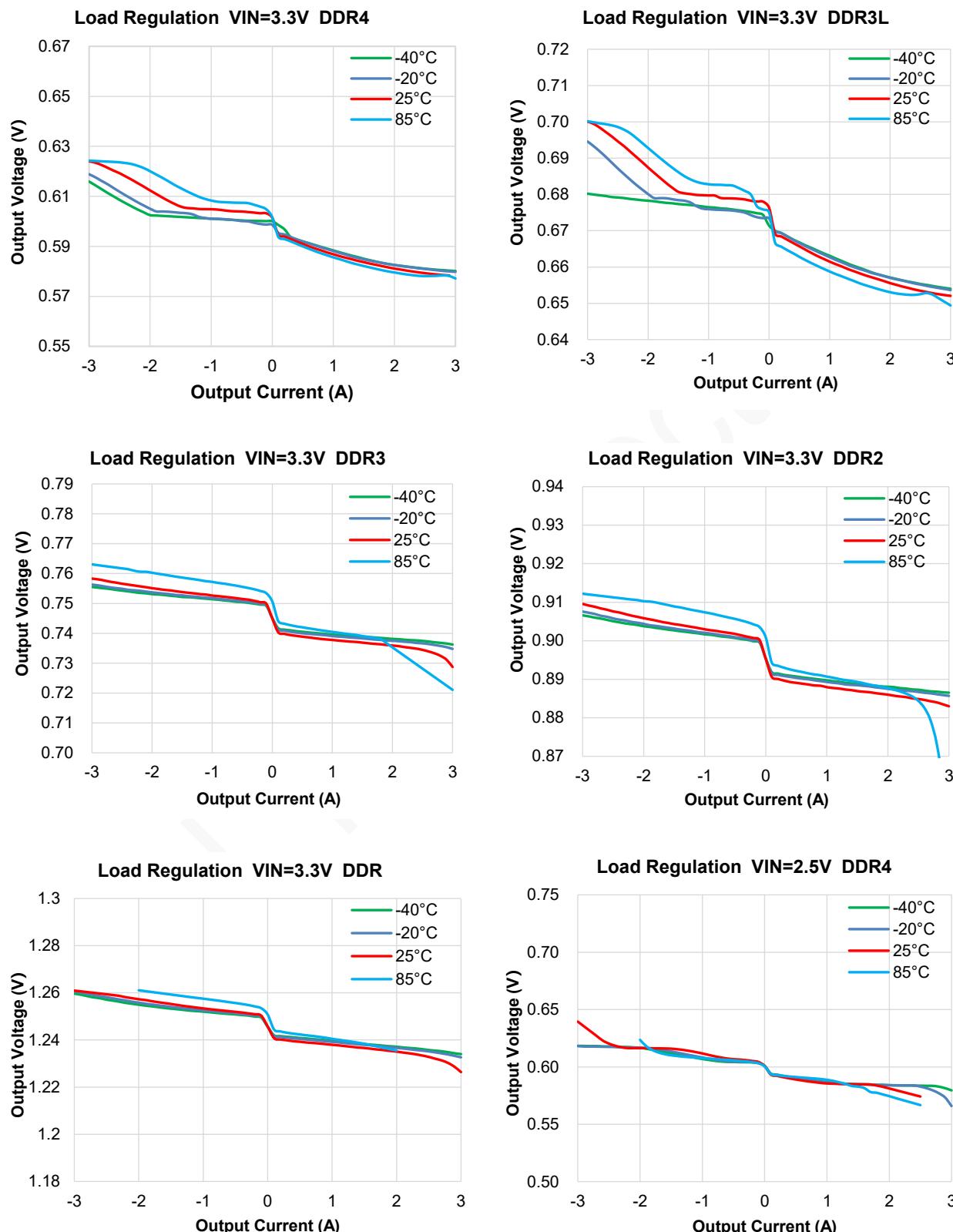


Figure 2. TMI62033 Block Diagram

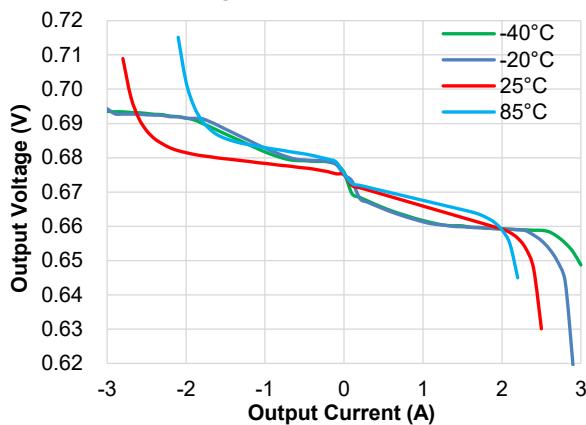
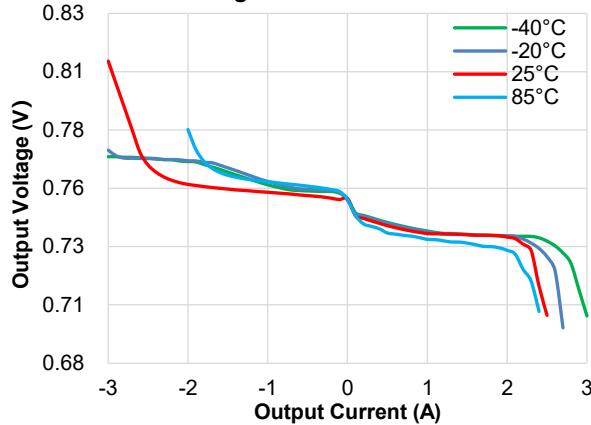
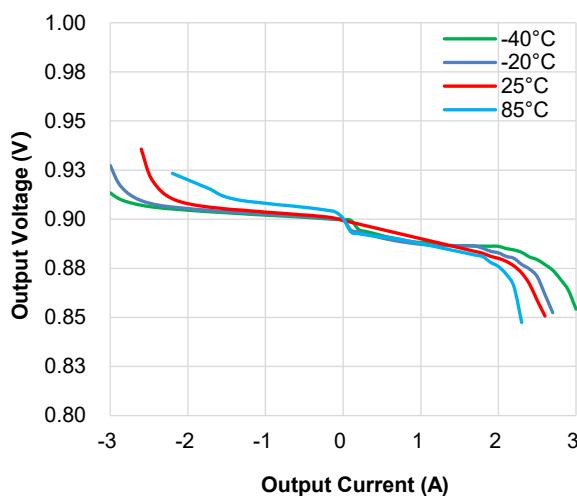
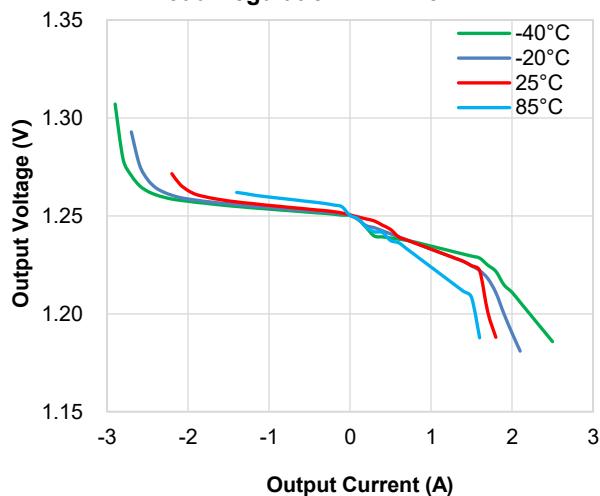
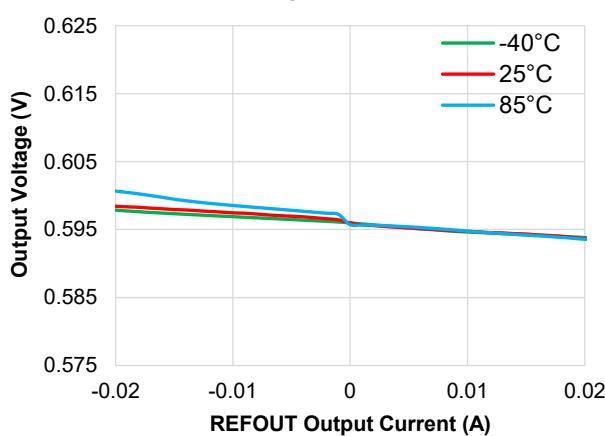
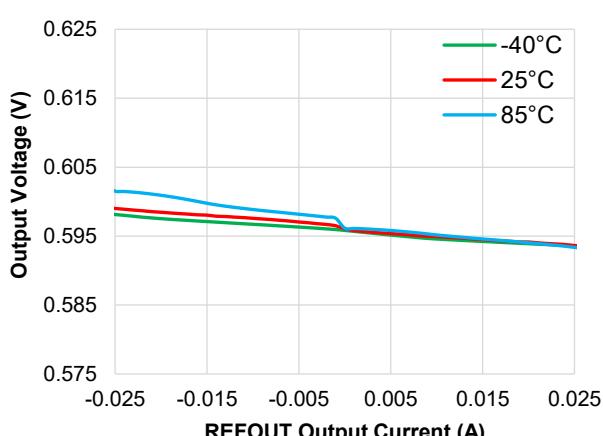
TYPICAL CHARACTERISTICS

$V_{IN} = 3.3V$, $V_{EN} = V_{VIN}$, $C_{OUT} = 3 \times 10\mu F$, $T_A = 25^\circ C$, and unless otherwise noted.



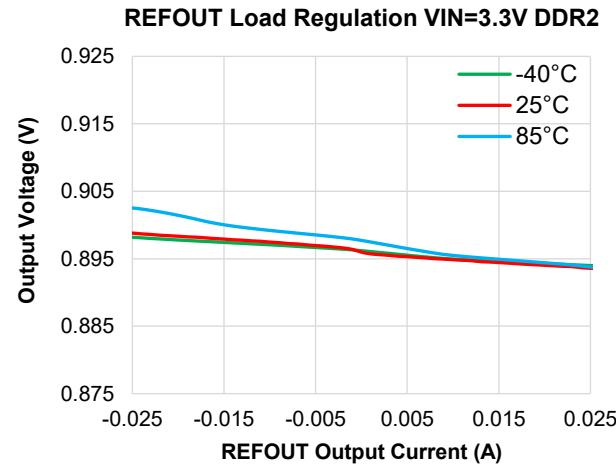
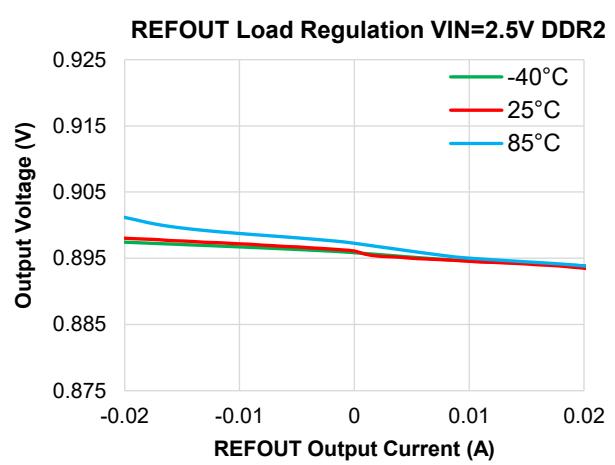
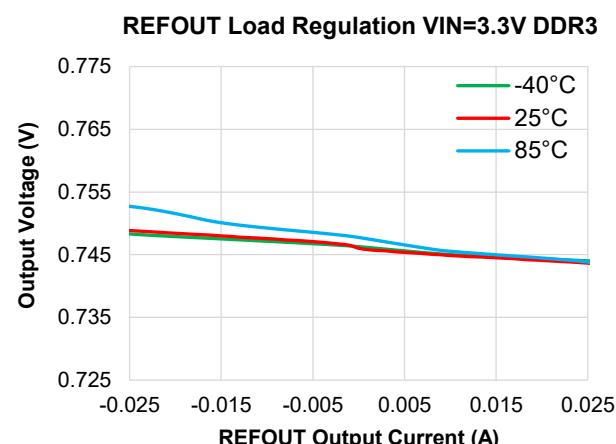
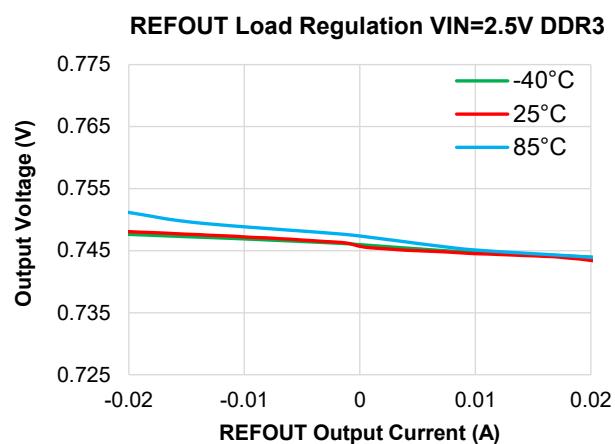
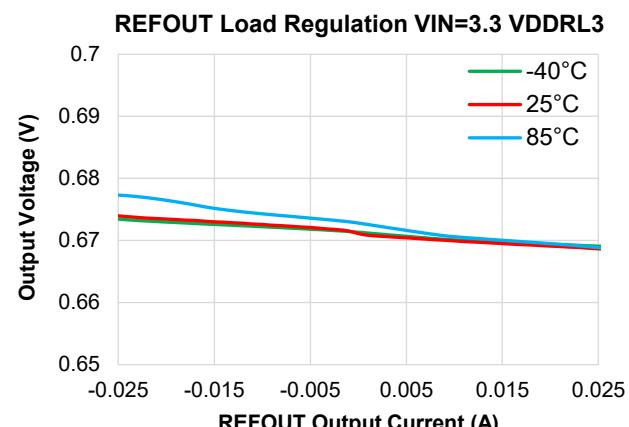
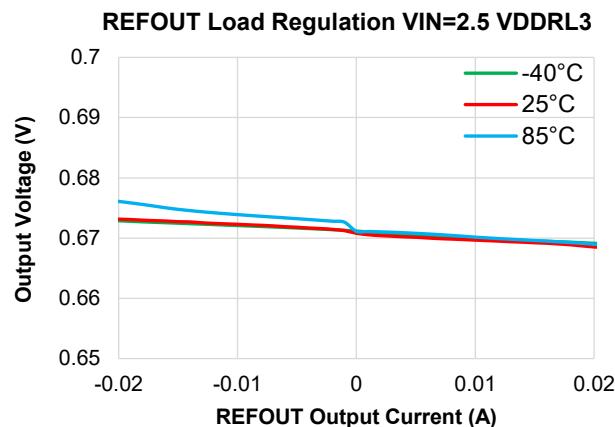
TYPICAL CHARACTERISTICS (continued)

$V_{IN} = 3.3V$, $V_{EN} = V_{VIN}$, $C_{OUT} = 3 \times 10\mu F$, $T_A = 25^\circ C$, and unless otherwise noted.

Load Regulation $V_{IN}=2.5V$ DDR3LLoad Regulation $V_{IN}=2.5V$ DDR3Load Regulation $V_{IN}=2.5V$ DDR2Load Regulation $V_{IN}=2.5V$ DDRREFOUT Load Regulation $V_{IN}=2.5V$ DDR4REFOUT Load Regulation $V_{IN}=3.3V$ DDR4

TYPICAL CHARACTERISTICS (continued)

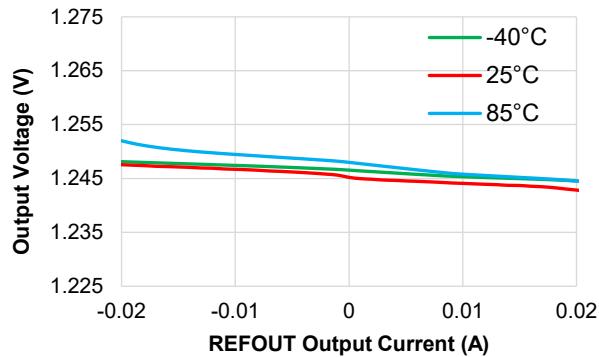
$V_{IN} = 3.3V$, $V_{EN} = V_{VIN}$, $C_{OUT} = 3 \times 10\mu F$, $T_A = 25^\circ C$, and unless otherwise noted.



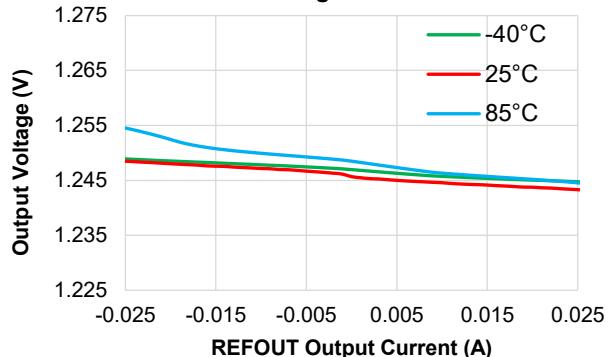
TYPICAL CHARACTERISTICS (continued)

$V_{IN} = 3.3V$, $V_{EN} = V_{VIN}$, $C_{OUT} = 3 \times 10\mu F$, $T_A = 25^\circ C$, and unless otherwise noted.

REFOUT Load Regulation $V_{IN}=2.5V$ DDR

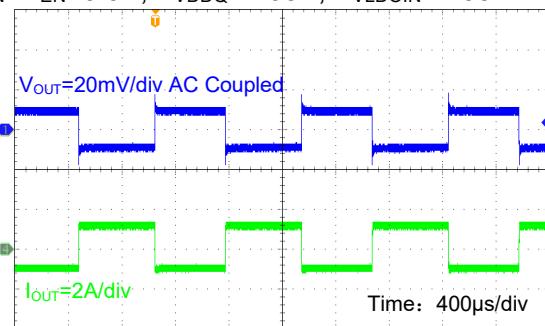


REFOUT Load Regulation $V_{IN}=3.3V$ DDR



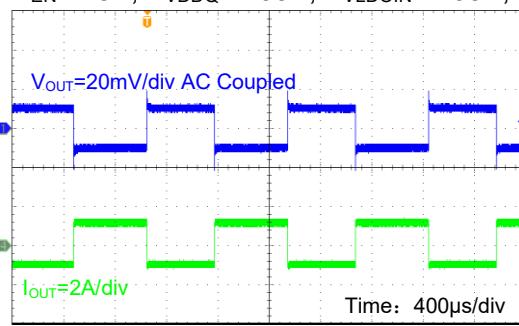
Load Transient

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.35V$, $V_{VLDOIN}=1.35V$



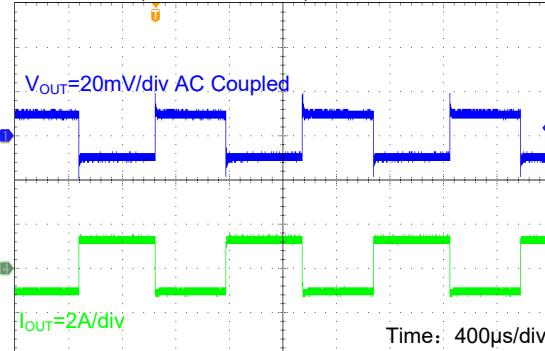
Load Transient

$V_{IN}=V_{EN}=2.5V$, $V_{VDDQ}=1.35V$, $V_{VLDOIN}=1.35V$,



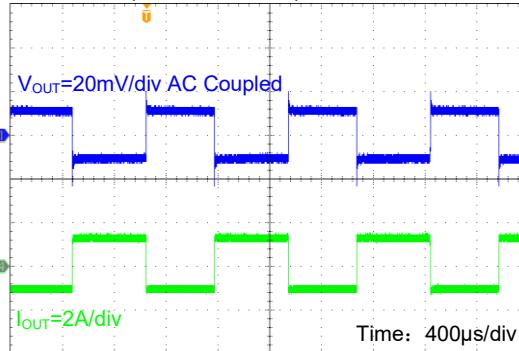
Load Transient

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.5V$, $V_{VLDOIN}=1.5V$



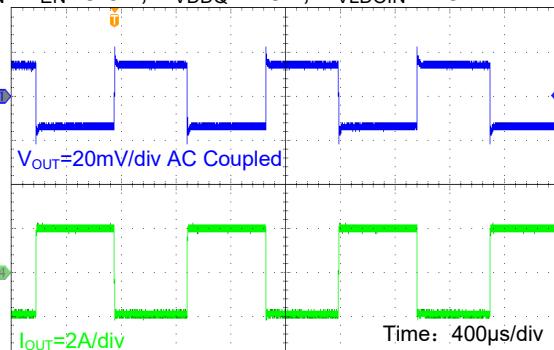
Load Transient

$V_{IN}=V_{EN}=2.5V$, $V_{VDDQ}=1.5V$, $V_{VLDOIN}=1.5V$



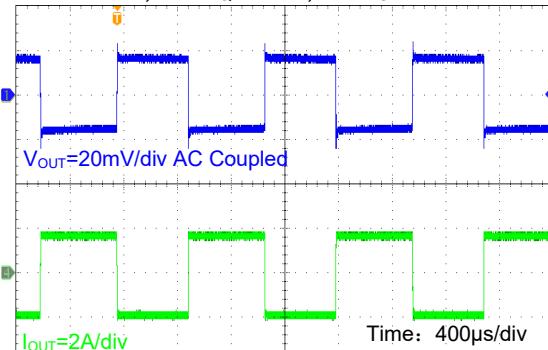
Load Transient

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$, $V_{VLDOIN}=1.8V$



Load Transient

$V_{IN}=V_{EN}=2.5V$, $V_{VDDQ}=1.8V$, $V_{VLDOIN}=1.8V$



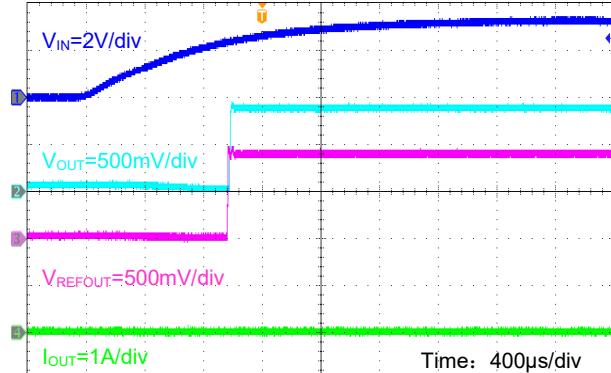
TYPICAL CHARACTERISTICS (continued)

$V_{IN} = 3.3V$, $V_{VLDOIN} = 1.8V$, $V_{REFIN} = 0.9V$, $V_{VOSNS} = 0.9V$, $V_{EN} = V_{IN}$, $C_{OUT} = 3 \times 10\mu F$, $T_A = 25^\circ C$

Input Power On

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

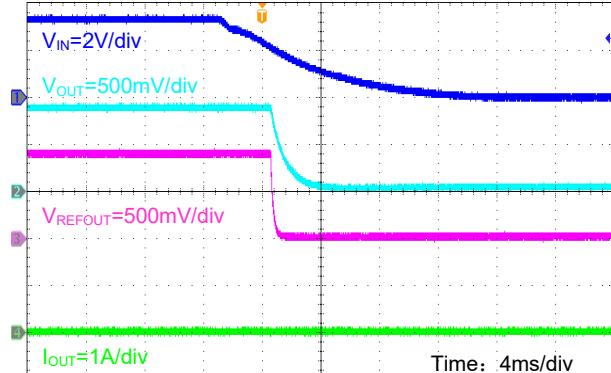
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Input Power Down

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

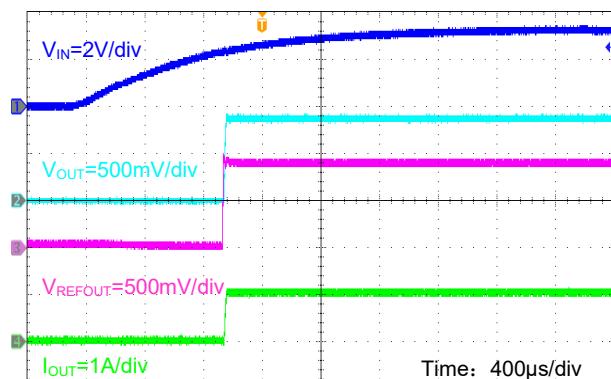
$V_{VLDOIN}=1.8V$, $I_{OUT}=0A$



Input Power On

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

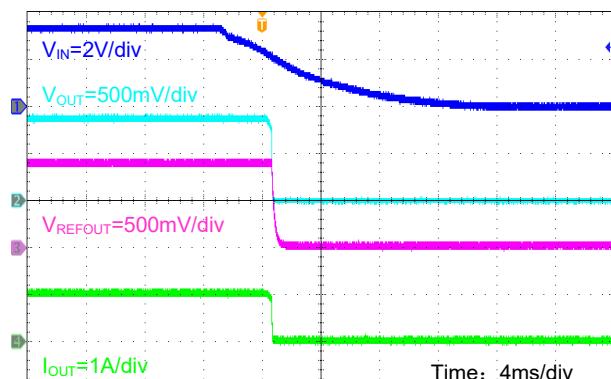
$V_{VLDOIN}=1.8V$, $I_{OUT}=1A$



Input Power Down

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

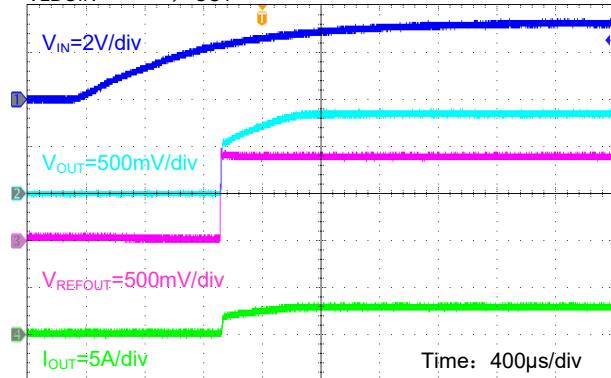
$V_{VLDOIN}=1.8V$, $I_{OUT}=1A$



Input Power On

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

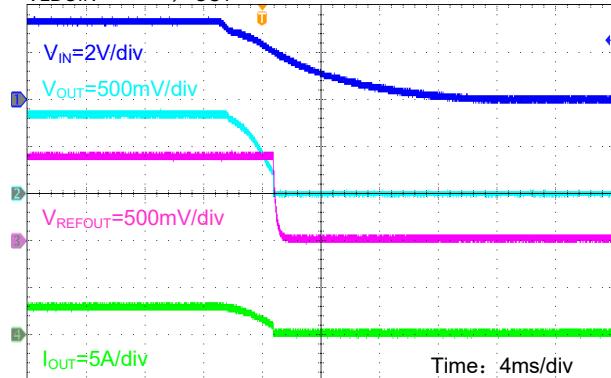
$V_{VLDOIN}=1.8V$, $I_{OUT}=3A$



Input Power Down

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

$V_{VLDOIN}=1.8V$, $I_{OUT}=3A$



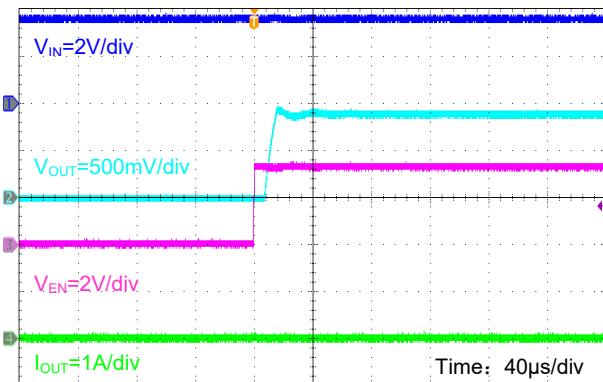
TYPICAL CHARACTERISTICS (continued)

$V_{IN} = 3.3V$, $V_{VLDOIN} = 1.8V$, $V_{REFIN} = 0.9V$, $V_{VOSNS} = 0.9V$, $V_{EN} = V_{IN}$, $C_{OUT} = 3 \times 10\mu F$, $T_A = 25^\circ C$

EN Enable Power On

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

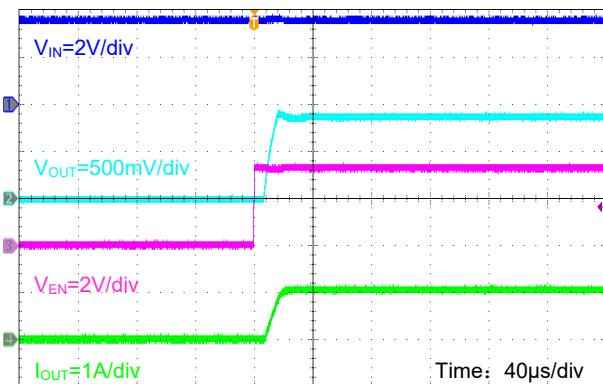
$V_{VLDOIN}=1.8V$, $I_{OUT}=0A$



EN Enable Power On

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

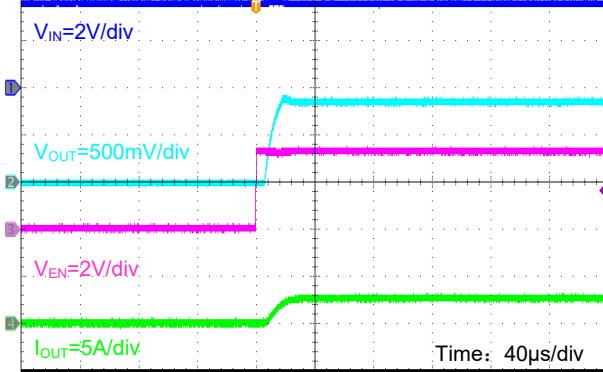
$V_{VLDOIN}=1.8V$, $I_{OUT}=1A$



EN Enable Power On

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

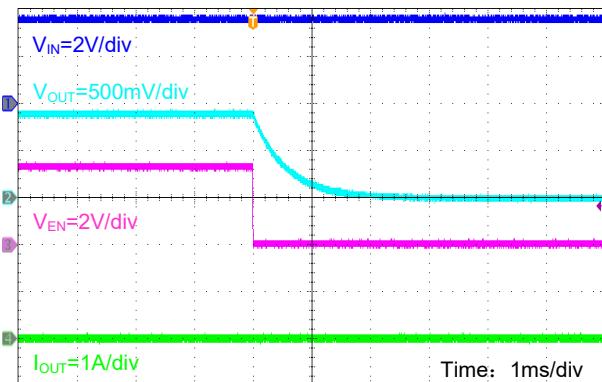
$V_{VLDOIN}=1.8V$, $I_{OUT}=3A$



EN Enable Power Down

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

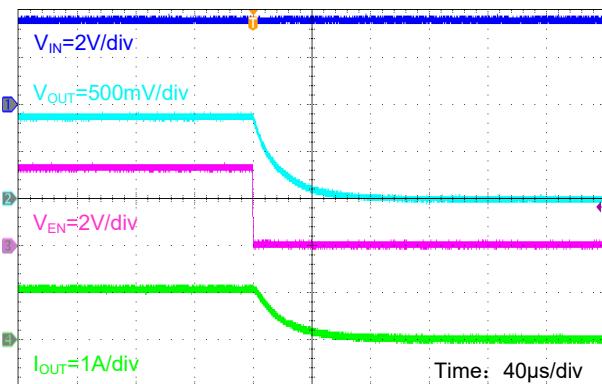
$V_{VLDOIN}=1.8V$, $I_{OUT}=0A$



EN Enable Power Down

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

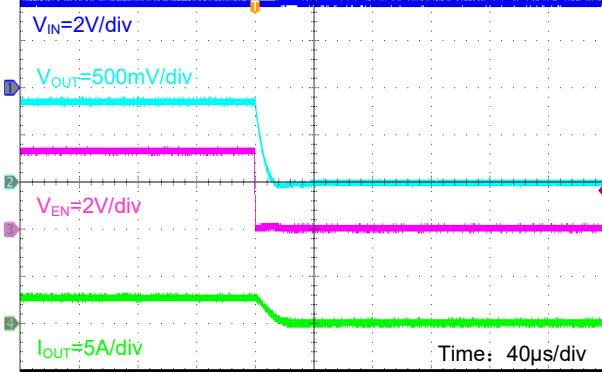
$V_{VLDOIN}=1.8V$, $I_{OUT}=1A$



EN Enable Power Down

$V_{IN}=V_{EN}=3.3V$, $V_{VDDQ}=1.8V$

$V_{VLDOIN}=1.8V$, $I_{OUT}=3A$



Operation Description

Overview

The TMI62033 is a 3A sink and source double data rate (DDR) termination regulator. It supports a remote sensing function and all power requirements for DDR, DDR2, DDR3, DDR3L, Low-Power DDR3 and DDR4 VTT bus termination.

The device maintains a fast transient response and requires a minimum output capacitance of only 20 μ F for low-cost, low-noise systems where space is a key consideration.

VO Pin (Sink and Source)

The TMI62033 is a 3A sink and source tracking DDR termination regulator specifically designed. The device integrates a high-performance, low-dropout (LDO) linear regulator that is capable of both sourcing and sinking current. The LDO regulator employs a fast feedback loop so that small ceramic capacitors can be used to support the fast load transient response. To get tight regulation with minimum effect of trace resistance, connect a remote sensing terminal, VOSNS, to the positive terminal of each output capacitor as a separate trace from the high current path from VO.

REFIN Pin

The output voltage, VO is regulated to REfout. When REFIN is configured for standard DDR termination applications, REFIN can be set by an external equivalent ratio voltage divider connected to the memory supply bus (VDDQ). The TMI62033 device supports REFIN voltages from 0.5V to 1.8V, for many types of low-power LDO applications.

REFOUT Pin

When it is configured for DDR termination applications, REfout generates the DDR VTT reference voltage for the memory application. It is capable of supporting both a sourcing and sinking load of 25mA. When the REFIN voltage is higher than rising UVLO threshold of REFIN and IN voltage is ready, there is voltage regulated at the REfout pin, which the REfout pin is independent with EN status.

EN Pin

When EN is driven high, the VO regulator begins normal operation. When the device drives EN low, VO discharges to GND through an internal MOSFET. REfout remains on when the device drives EN low. Ensure that the EN pin voltage remains lower than or equal to VIN at all times.

Soft-Start

A current clamp implements the soft-start function of the VO pin. The current clamp allows the output capacitors to be charged with low and constant current, providing a linear ramp-up of the output voltage. When VO is outside of the power good window, the current clamp level is one-half of the full overcurrent limit (OCL) level. When VO rises or falls within the PGOOD window, the current clamp level switches to the full OCL level. The soft-start function is completely symmetrical and the

overcurrent limit works for both directions. The soft-start function works not only from GND to the REFOUT voltage, but also from VLDOIN to the REFOUT voltage.

PGOOD Pin

The TMI62033 device provides an open-drain PGOOD output that goes high when the VO output is within $\pm 20\%$ of REFOUT. When output voltage enters the power-good window, the PG pin turns to high output impedance, and PG is pulled up to high-voltage level after 2ms delay to indicate the output voltage is ready.

A pull-up resistor is recommended with a value between $1k\Omega$ and $100k\Omega$, placed between PGOOD and a stable active supply voltage rail is required.

UVLO Protection of VIN

The TMI62033 monitors VIN voltage. When the VIN voltage is lower than the UVLO threshold voltage, both the VO and REFOUT regulators are powered off. This shutdown is a non-latch protection.

Over Current Limit (OCL)

The LDO has a constant overcurrent limit (OCL). The OCL level reduces by one-half when the output voltage is not within the power good window. This reduction is a non-latch protection.

Thermal Shutdown

The TMI62033 monitors junction temperature. If the device junction temperature exceeds the threshold value, (typically 155°C), the VO and REFOUT regulators both shut off, discharged by the internal discharge MOSFETs. This shutdown is a non-latch protection.

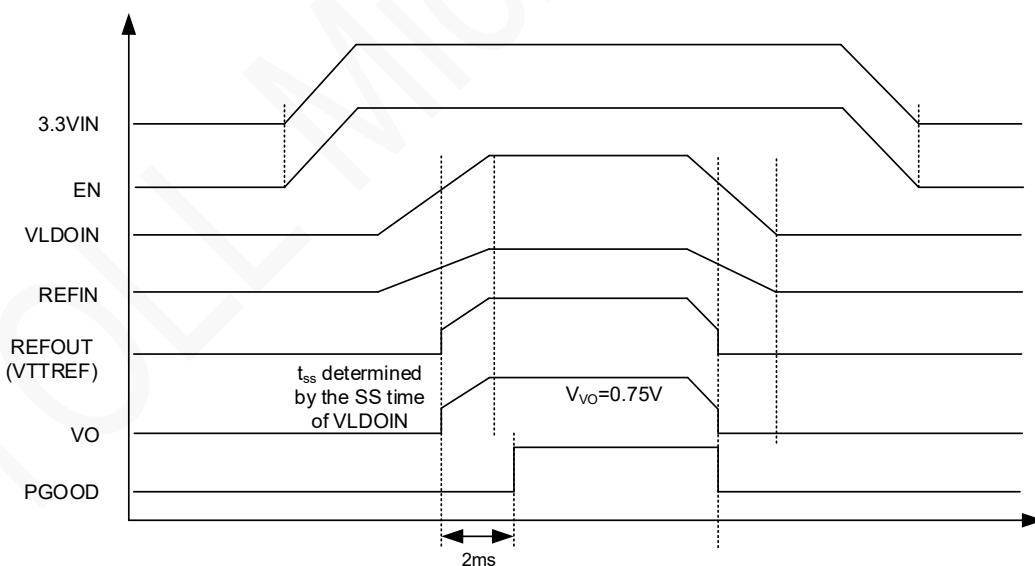


Figure 3. Typical Timing Diagram of Tracking Start-up and Shutdown

Tracking Start-up and Shutdown

The TMI62033 also supports tracking start-up and shutdown when the EN pin is tied directly to the system bus and not used to turn on or turn off the device. During tracking start-up, VO follows REfout once REFIN voltage is greater than 0.39V. REFIN follows the rise of VDDQ rail through a voltage divider. The typical soft-start time (t_{ss}) for the VDDQ rail is approximately 3ms, however it may vary depending on the system configuration. The soft-start time of the VO output no longer depends on the OCL setting, but it is a function of the soft-start time of the VDDQ rail. PGOOD is asserted 2ms after V_{vo} is within $\pm 20\%$ of REfout. During tracking shutdown, the VO pin voltage falls following REfout until REfout reaches 0.33 V. When REfout falls below 0.33 V, the internal discharge MOSFETs turn on and quickly discharge both REfout and VO to GND. PGOOD is deasserted when VO is beyond the $\pm 20\%$ range of REfout. Figure 3 shows the typical timing diagram for an application that uses tracking start-up and shutdown.

Layout

Layout Guidelines

Consider the following points before starting the TMI62033 device layout design.

- Place the input capacitors as close to VDLOIN pin as possible with short and wide connection. Place the output capacitor as close to VO pin as possible with short and wide connection. Place a ceramic capacitor with a value of at least 20 μ F as close to VO pin if the rest of output capacitors need to be placed on the load side.
- Connect the VOSNS pin to the positive node of output capacitors as a separate trace. In DDR VTT application, connect the VO sense trace to DIMM side to ensure the VTT voltage at DIMM side is well regulated.
- Consider adding low-pass filter at VOSNS if the VO sense trace is very long. Connect the GND pin and PGND pin to the thermal pad directly.
- TMI62033 uses its thermal pad to dissipate heat. In order to effectively remove heat from TMI62033 package, place numerous ground vias on the thermal pad. Use large ground copper plane, especially the copper plane on surface layer, to pour over those vias on thermal pad.

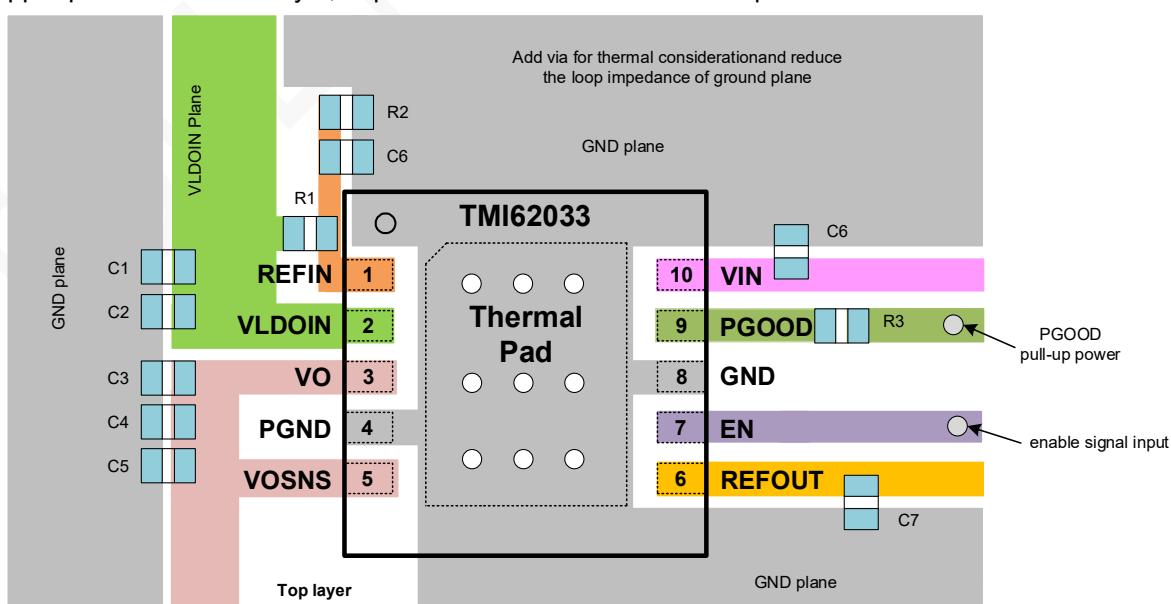
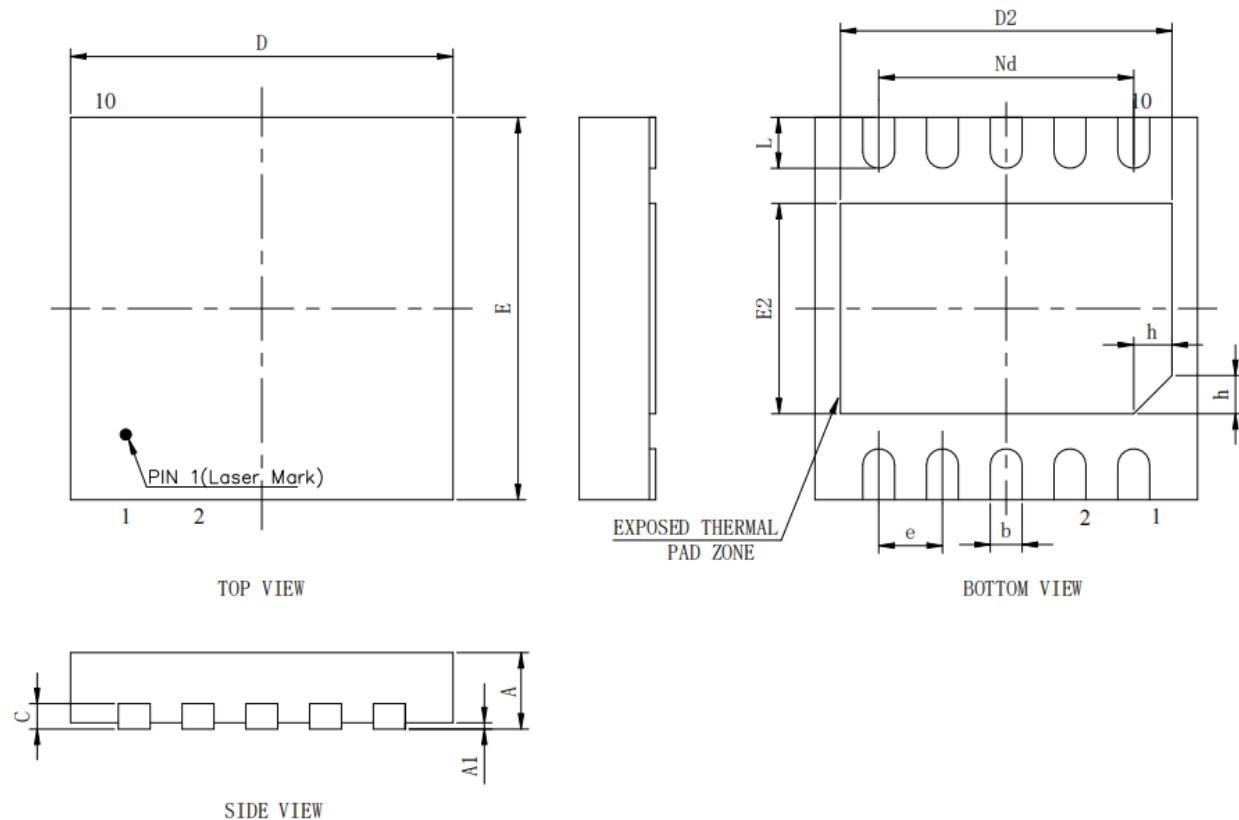


Figure 4. Layout Recommendation

Package Information

DFN3x3-10



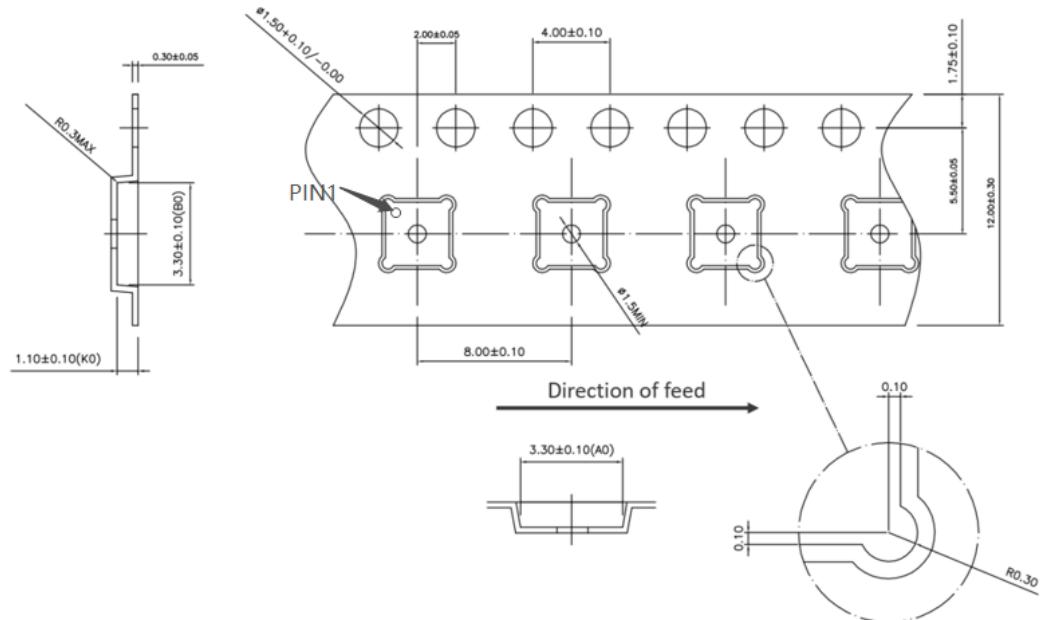
Symbol	Dimensions In Millimeters			Symbol	Dimensions In Millimeters			Unit: mm
	Min	Nom	Max		Min	Nom	Max	
A	0.85	0.90	0.95	L	0.30	0.40	0.50	
A1	0	0.02	0.05	h	0.20	0.25	0.30	
b	0.20	0.25	0.30	e	0.50BSC			
D	2.90	3.00	3.10	Nd	2.00BSC			
E	2.90	3.00	3.10	c	0.20REF			
D2	2.40	2.50	2.60					
E2	1.45	1.55	1.65					

Note:

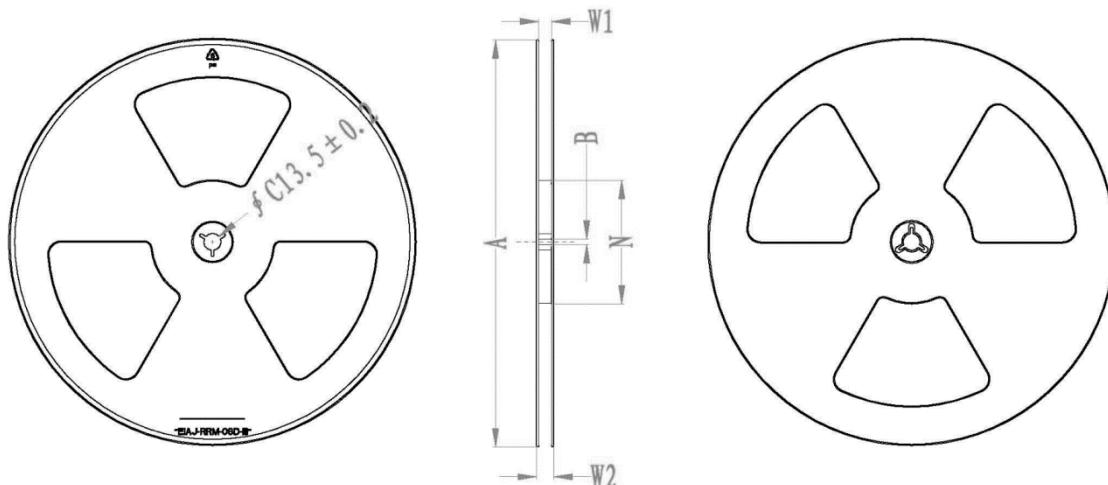
All dimensions are in millimeters.

TAPE AND REEL INFORMATION

TAPE DIMENSIONS:



REEL DIMENSIONS:



Unit: mm

Ø A	Ø C	B	W1	W2	N
330±1.0	13.5±0.2	4.7±0.5	13.4±0.5	17.4±0.5	100±0.5

Note:

All Dimensions are in Millimeter

Quantity of Units per Reel is 5000

MSL level is level 3.

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